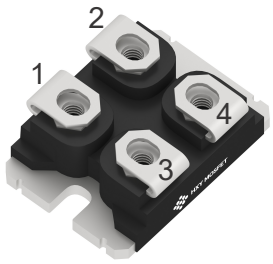
HXYS125N120Q

SiC Power MOSFET N-Channel Enhancement Mode

Features

- 3rd generation SiC MOSFET technology
- Optimized package with separate driver source pin
- High blocking voltage with low on-resistance
- High-speed switching with low capacitances
- Fast intrinsic diode with low reverse recovery (Q_{rr})
- Halogen free, RoHS compliant



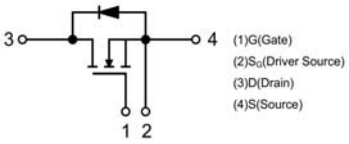
SOT-227

Benefits

- Reduce switching losses and minimize gate ringing
- Higher system efficiency
- Reduce cooling requirements
- Increase power density
- Increase system switching frequency

Applications

- Renewable energy
- EV battery chargers
- High voltage DC/DC converters
- Switch Mode Power Supplies



Ordering Part Number	Package	Brand
HXYS125N120Q	SOT-227	HXY MOSFET

Maximum Ratings (T_C = 25 ˚C unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-source voltage	V_{DS}	1200	V
Continuous drain current T_C = 25°C， V_{GS} = 18V T_C = 100°C， V_{GS} = 18V	I_D	 125 90	A
Pulsed drain current (T_C = 25°C, t_p limited by T_{jmax})	$I_{D\ pulse}$	250	A
Gate-Source voltage	V_{GS}	-4/+18	V
Gate-Source voltage（Absolute maximum values）	V_{GSmax}	-8/+22	V
Power dissipation (T_C = 25°C)	P_{tot}	681	W
Operating junction and storage temperature	T_j , T_{stg}	-40…+175	°C

●Example of acceptable V_{GS} waveform

Thermal Resistance

Parameter	Symbol	Value	Unit
Thermal resistance, junction – case. Max	R_{thJC}	0.22	°C/W

Electrical Characteristics (at Tj = 25 °C, unless otherwise specified)

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Static Characteristic						
Drain-source breakdown voltage	BV_{DSS}	1200	-	-	V	V_{GS}=0V, I_D=250uA
Gate threshold voltage	$V_{GS(th)}$	2	3	4	V	V_{DS}=V_{GS},I_D=25mA
Zero gate voltage drain current	I_{DSS}	- -	1 10	50 -	μA	V_{DS}=1200V,V_{GS}=0 V T_C=25°C T_C=175°C
Gate-source leakage current	I_{GSS}	-		200	nA	V_{GS}=18V,V_{DS}=0V
Drain-source on-state resistance	$R_{DS(on)}$	- -	15 29	22 -	mΩ	V_{GS}=18V, I_D=80A, T_J=25°C T_J=175°C
Transconductance	g_{fs}	-	43	-	S	V_{DS}=20V,I_D=40A

Dynamic Characteristic

Input Capacitance	C_{iss}	-	4508	-	pF	V_{DS} = 1000V V_{GS} = 0V T_J = 25°C V_{AC} = 25mV f = 1MHz
Output Capacitance	C_{oss}	-	214	-		
Reverse Transfer Capacitance	C_{rss}	-	26	-		
Gate Total Charge	Q_G	-	222	-	nC	V_{DS} = 800V V_{GS} = 0/18V I_D = 80A
Gate-Source charge	Q_{gs}	-	46.4	-		
Gate-Drain charge	Q_{gd}	-	77.6	-		
Turn-On Switching Energy	E_{ON}	-	2.29	-	mJ	V_{DD} = 800V V_{GS} = -4/+18V I_D=80A R_G = 5Ω L = 120uH
Turn-Off Switching Energy	E_{OFF}	-	0.63	-		
Turn-on delay time	$t_{d(on)}$	-	49.2	-	ns	
Rise time	t_r	-	14.2	-		
Turn-off delay time	$t_{d(off)}$	-	21.7	-		
Fall time	t_f	-	11.3	-		
Gate resistance	R_G	-	0.9	-	Ω	V_{AC} = 25mV, f=1MHz

Body Diode Characteristic

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Body Diode Forward Voltage	V_{SD}		4.4		V	V_{GS}=-4V,I_{SD}=40A, T_J=25°C
			3.9			V_{GS}=-4V,I_{SD}=40A, T_J=175°C
Body Diode Reverse Recovery Time	t_{rr}	-	29.6	-	ns	V_R = 800V I_D = 80A di/dt = 1000A/μS T_J = 25°C
Body Diode Reverse Recovery Charge	Q_{rr}	-	272	-	nC	

Typical Performance Characteristics

Fig 1. Output Characteristic (T_J=-55°C)

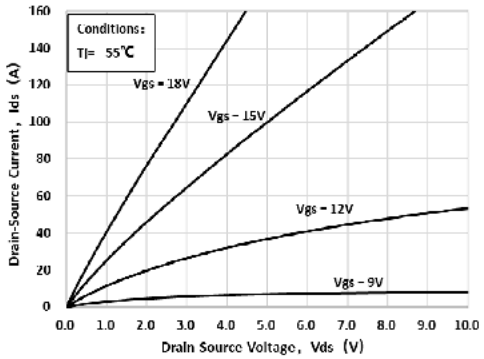


Fig 2. Output Characteristic (T_J=25°C)

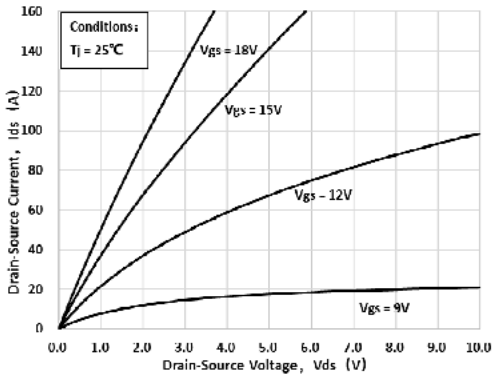


Fig 3. Output Characteristic (T_J=175°C)

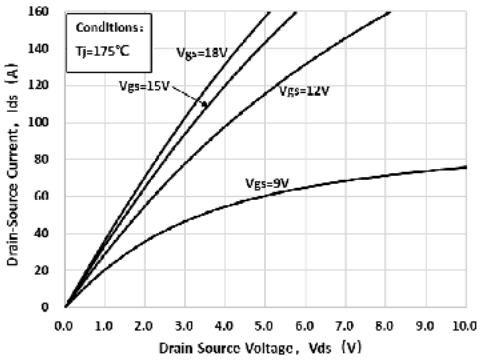


Fig 4: Rdson Vs Ids Characteristic

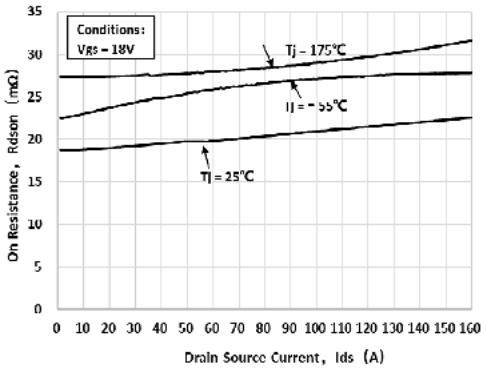


Fig 5: Rds(on) vs. Temperature

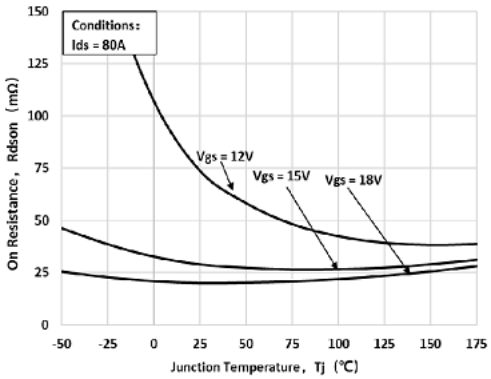


Fig 6: Transfer Characteristic

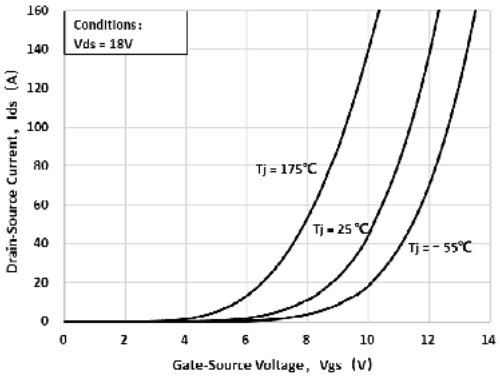


Fig 7: Body-diode Characteristic (T_J=-55°C)

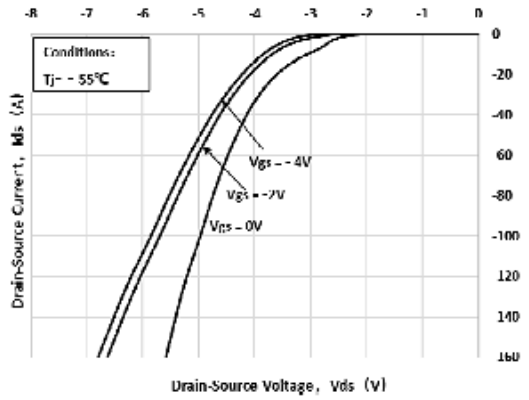


Fig 8: Body-diode Characteristic (T_J=25°C)

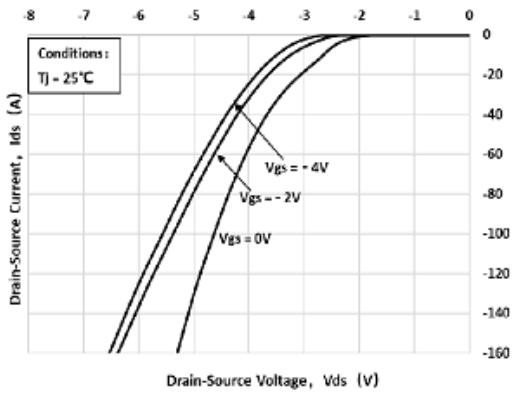


Fig 9: Body-diode Characteristic (T_J=175°C)

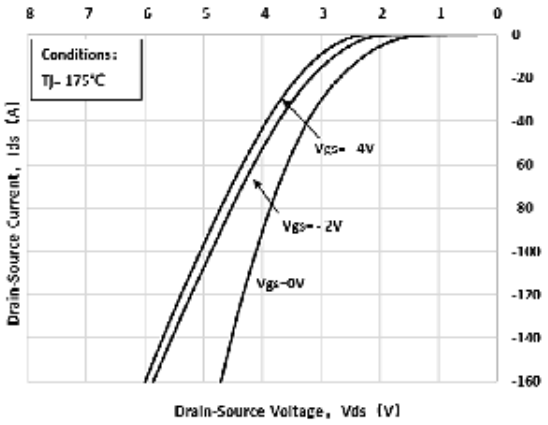


Fig 10: V_{TH} Vs T_J Temperature Characteristic

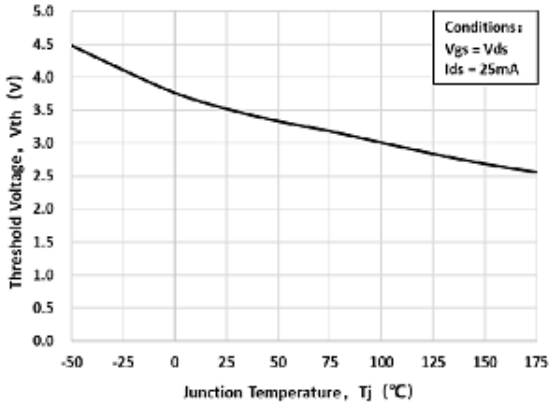


Fig 11: Gate Charge Characteristics

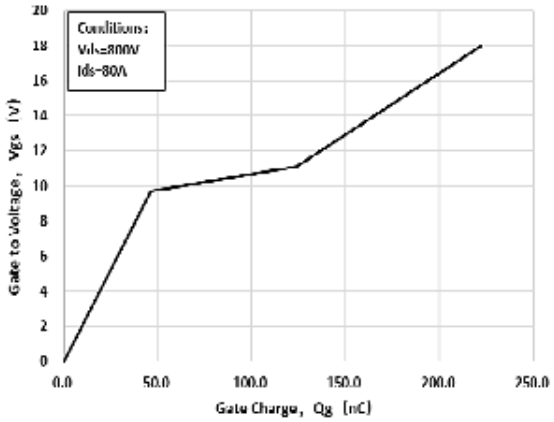


Fig 12: 3rd Quadrant Characteristic(T_J=-55°C

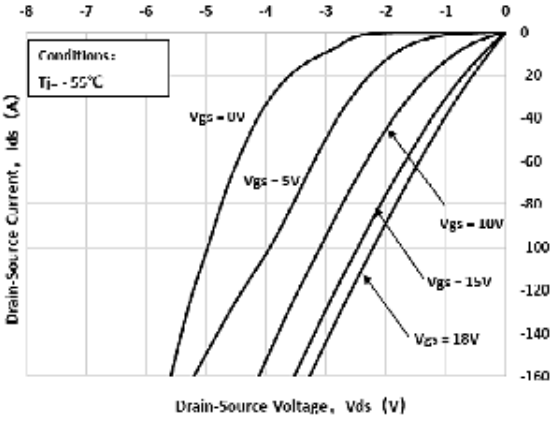


Fig 13: 3rd Quadrant Characteristic(T_J=25℃)

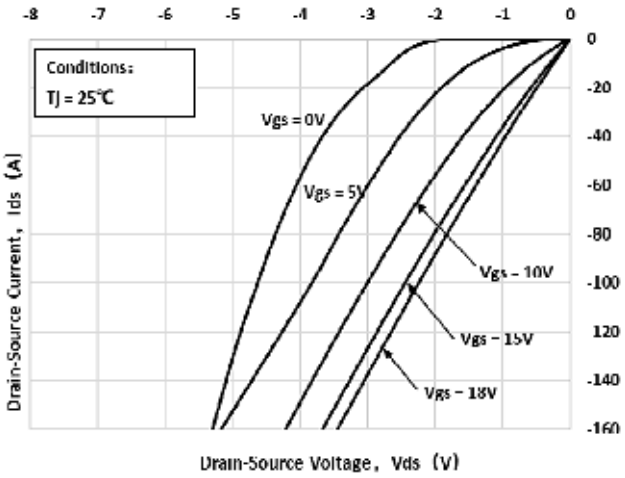


Fig 14: 3rd Quadrant Characteristic(T_J=175℃)

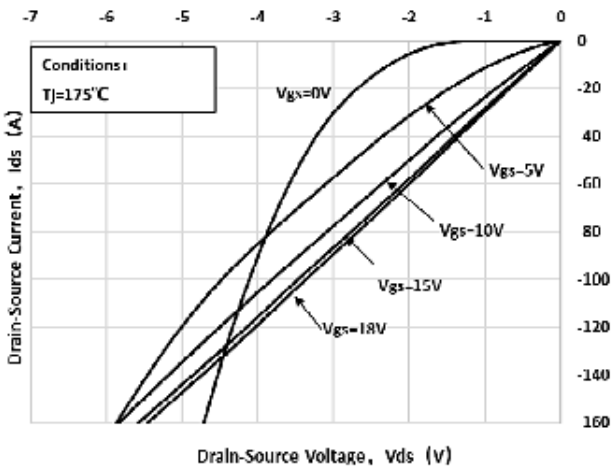


Fig 15: Capacitance Characteristic

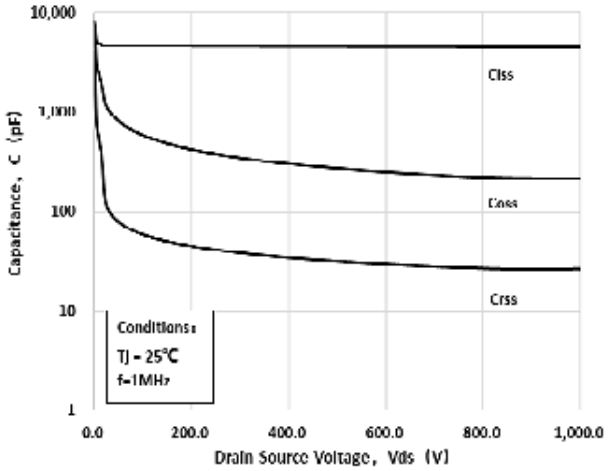
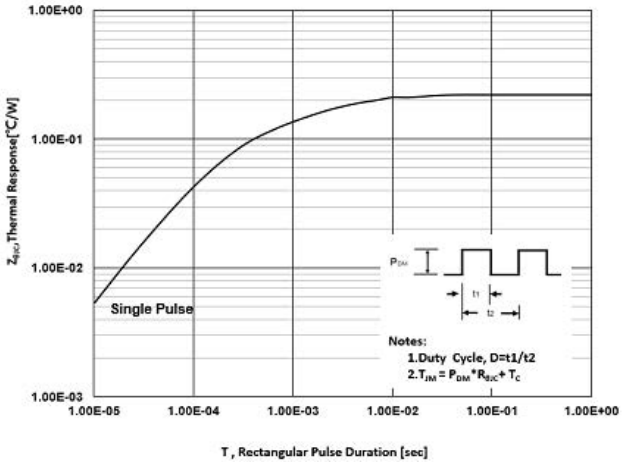


Fig 17: Transient Thermal Impedance



Test Circuit & Waveform

Figure A. Definition of switching times

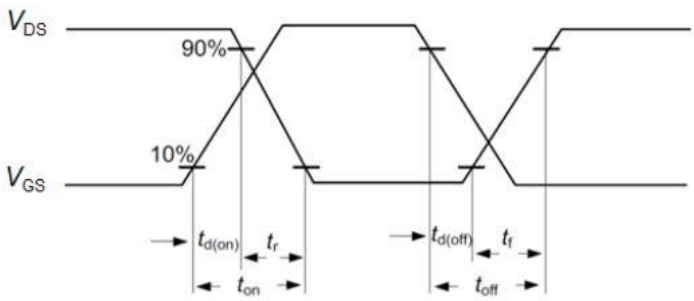


Figure B. Dynamic test circuit

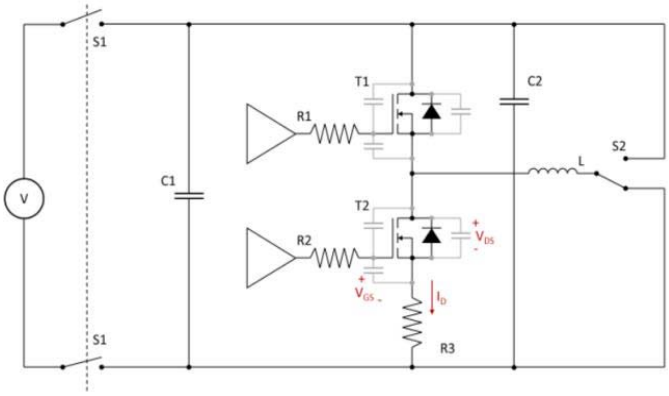
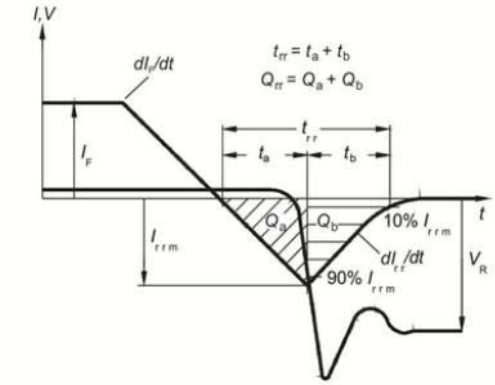
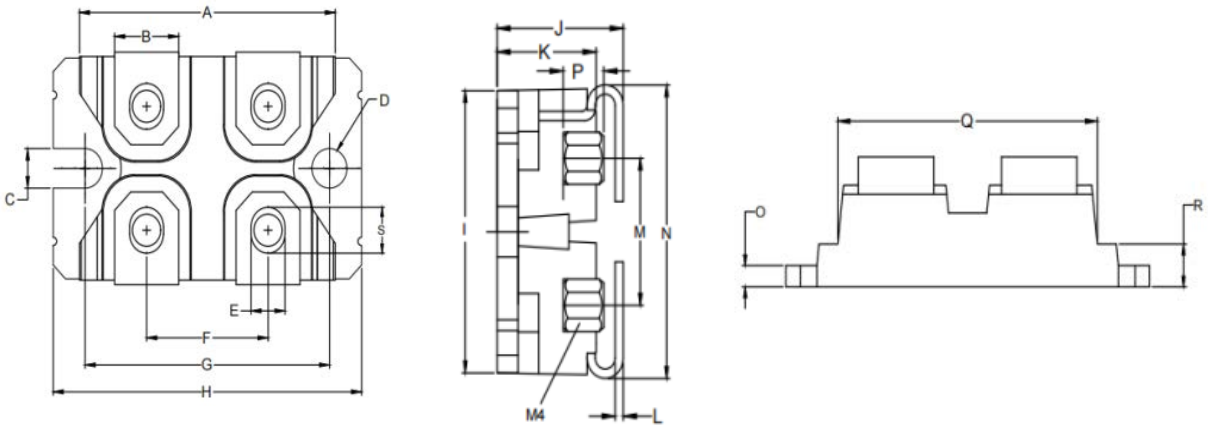


Figure C. Definition of body diodeswitching characteristics



Package
Dimensions
Package SOT-227



DiM	Millimeter	
	Min	Max
A	31.40	31.60
B	7.70	8.10
C	4.20	4.40
D	4.20	4.40
E	4.10	4.30
F	14.90	15.10
G	30.10	30.20
H	38.00	38.40
I	23.80	24.20
J	12.20	12.70
K	9.40	9.60
L	0.75	0.85
M	12.40	12.80
N	24.50	25.40
O	1.90	2.10
P	3.10	3.95
Q	26.60	27.00
R	3.80	4.20
S	5.10	5.40

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